

Surface mount
Schottky

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time $I_F = A$ $I_R = A$ $I_{RR} = A$ t_{rr} ns	Max. forward voltage $V_F^{(2)}$
CS 10D	20	20	/	< 0,50
CS 20D	40	40	/	< 0,50
CS 30D	60	60	/	< 0,70
CS 40D	80	80	/	< 0,79
CS 50D	100	100	/	< 0,79

Bridge rectifiers

CS 10D ... CS 50D

Forward Current: 1 A

Reverse Voltage: 10 to 50 V

Publish Data

Features

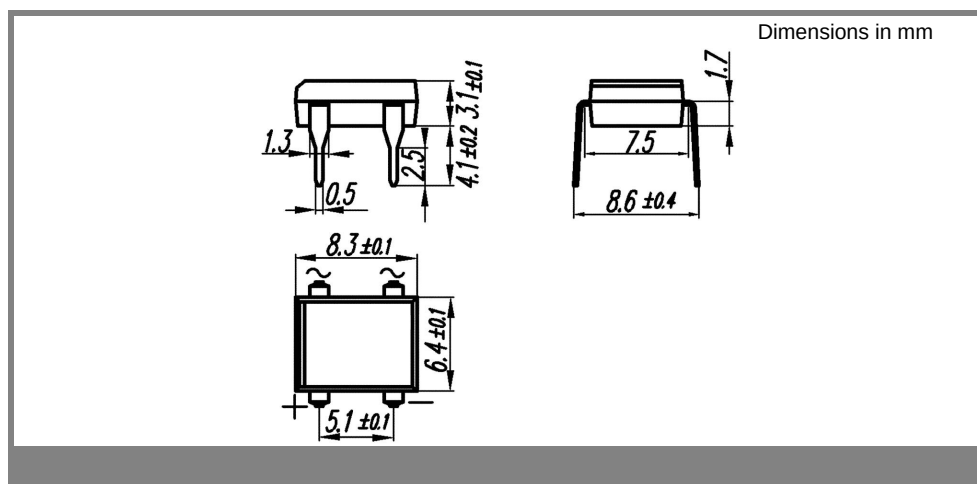
- Standard packaging into plastic tubes

Mechanical Data

- Plastic case SO-DIL 8.5x6.6x3.1 mm
- Weight approx. 0.6 g
- 2) $I_F = 1A$, $T_j = 25^\circ C$

Absolute Maximum Ratings		$T_c = 25^\circ C$ unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50^\circ C$ ¹⁾	1	A
I_{FRM}	Repetitive peak forward current $f > 15 Hz$ ¹⁾	10	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	40	A
i^2t	Rating for fusing, $t < 10 ms$ ³⁾	8	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾	60	K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾		K/W
T_j	Operating junction temperature	-50 ... +150°C	°C
T_s	Storage temperature	-50 ... +150°C	°C

Characteristics		$T_c = 25^\circ C$ unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25^\circ C$; $V_R = V_{RRM}$	0,5	mA
	$T_j = 100^\circ C$; $V_R = V_{RRM}$	5	mA
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)		μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_j = ^\circ C$; inductive load switched off)		mJ



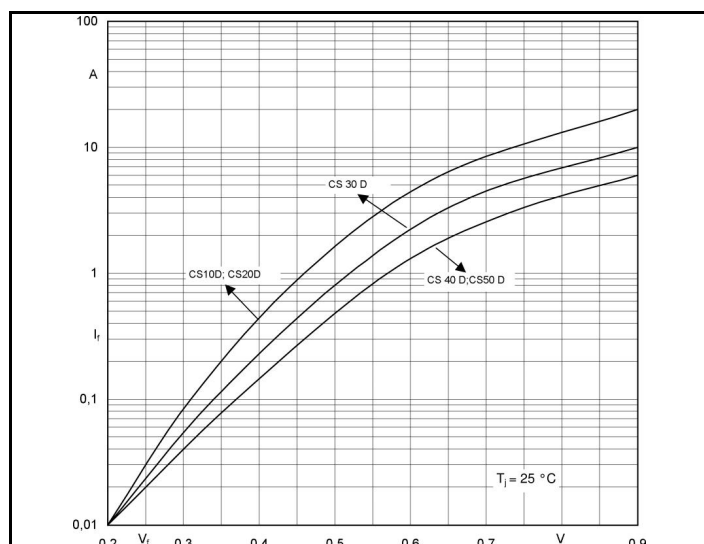


Fig. 1 : Forward characteristic (typical values)

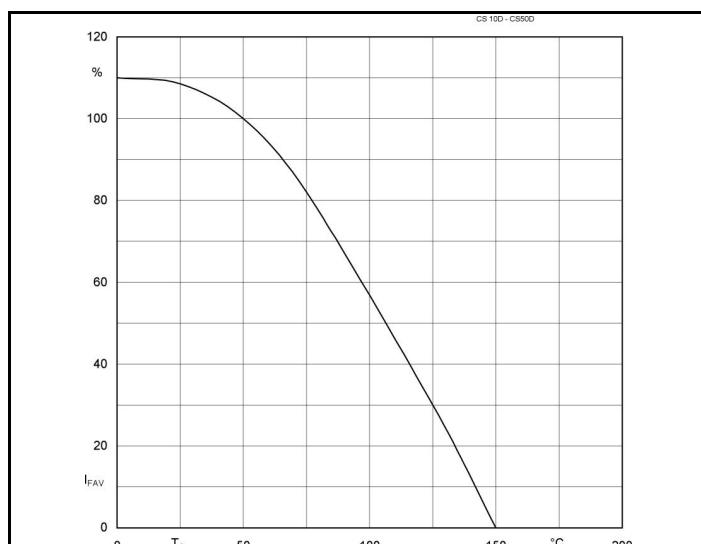


Fig. 2 : Rated forward current vs. ambient temperature

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